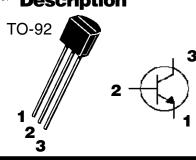
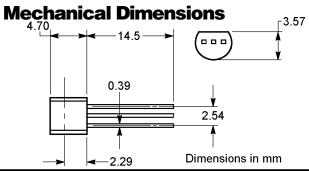


**NPN General Purpose Transistor** 

12222A





Maximum Ratings					
Ratings	Symbol	Value	Units		
Collector - Emitter Voltage	V <sub>CEO</sub>	40	V		
Collector - Base Voltage	V <sub>CBO</sub>	75	V		
Emitter - Base Voltage	$V_{EBO}$	6.0	V		
Collector Current (Continuous)	I <sub>c</sub>	600	mA		
Total Device Dissipation $T_{_{A}}=25^{\circ}C$	$P_{D}$	625	mW		
Junction and Storage Temperature	$T_{J},T_{STG}$	-55 to 150	°C		

**Electrical Characteristics** 

Electrical Characteristics				
Characteristic	Symbol	Min	Max	Unit
Collector - Emitter Breakdown Voltage (Note 3) $(I_c = 10\text{mA})$	V <sub>BR(CEO)</sub>	40		V
Collector - Base Breakdown Voltage ( $I_c = 10\mu A$ )	V <sub>BR(CBO)</sub>	75		V
Emitter - Base Breakdown Voltage $(I_E = 10\mu\text{A})$	$V_{BR(EBO)}$	6.0		V
Base Cutoff Current $(V_{CB} = 60V)$	I <sub>CBO</sub>		10	nA
Collector Cutoff Current $(V_{CE} = 60V, V_{EB(OFF)} = 3.0V)$	I <sub>CEX</sub>		10	nA
Emitter Cutoff Current (V <sub>EB</sub> = 3.0V)	I <sub>EBO</sub>		10	nA
DC Current Gain	H <sub>FE</sub>	35 50 75 100 40	  300 	
Collector - Emitter Saturation Voltage ( $I_c = 150 \text{ mA}, I_B = 15 \text{ mA}$ ) ( $I_c = 500 \text{ mA}, I_B = 50 \text{ mA}$ )	V <sub>CE(sat)</sub>		0.3 1.0	V
Base - Emitter Saturation Voltage ( $I_c = 150$ mA, $I_B = 15$ mA) ( $I_c = 500$ mA, $I_B = 50$ mA)	V <sub>BE(sat)</sub>		1.2 2.0	V
Current - Gain - Bandwidth Product (Note 4) $(I_C = 20 \text{ mA}, V_{CB} = 20 \text{ V}, f = 100 \text{ MHz})$	f <sub>T</sub>	300		MHz

## Classification of h<sub>FF4</sub>

Rank	Α	В	
Range	100-210	190-300	



## 2N2222A NPN General Purpose Transistor

